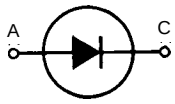
IXYS

Fast Recovery Epitaxial Diode (FRED)

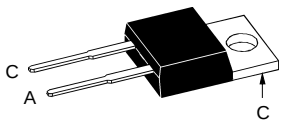
DSEI 20

I_{FAVM} = 17 A
V_{RRM} = 1200 V
t_{rr} = 40 ns

V_{RSM} V	V_{RRM} V	Type
1200	1200	DSEI 20-12A



TO-220 AC



A = Anode, C = Cathode

Symbol	Test Conditions		Maximum Ratings	
I_{FRMS}	$T_{VJ} = T_{VJM}$		70	A
I_{FAVM} ①	T_C = 85°C; rectangular, d = 0.5		17	A
I_{FRM}	t_P < 10 µs; rep. rating, pulse width limited by T_{VJM}		220	A
I_{FSM}	T_{VJ} = 45°C;	t = 10 ms (50 Hz), sine	130	A
		t = 8.3 ms (60 Hz), sine	140	A
	T_{VJ} = 150°C;	t = 10 ms (50 Hz), sine	110	A
		t = 8.3 ms (60 Hz), sine	120	A
I^2t	T_{VJ} = 45°C	t = 10 ms (50 Hz), sine	85	A^2s
		t = 8.3 ms (60 Hz), sine	80	A^2s
	T_{VJ} = 150°C;	t = 10 ms (50 Hz), sine	60	A^2s
		t = 8.3 ms (60 Hz), sine	60	A^2s
T_{VJ}			-40...+150	°C
T_{VJM}			150	°C
T_{stg}			-40...+150	°C
P_{tot}	T_C = 25°C		78	W
M_d	Mounting torque		0.4...0.6	Nm
Weight			2	g

Symbol	Test Conditions		Characteristic Values typ.	max.	
I_R	T_{VJ} = 25°C	$V_R = V_{RRM}$		750	µA
	T_{VJ} = 25°C	$V_R = 0.8 \cdot V_{RRM}$		250	µA
	T_{VJ} = 125°C	$V_R = 0.8 \cdot V_{RRM}$		7	mA
V_F	I_F = 12 A;	T_{VJ} = 150°C		1.87	V
		T_{VJ} = 25°C		2.15	V
V_{T0}	For power-loss calculations only			1.65	V
r_T	$T_{VJ} = T_{VJM}$			18.2	mΩ
R_{thJC}				1.6	K/W
R_{thJA}				60	K/W
t_{rr}	I_F = 1 A; -di/dt = 100 A/µs; V_R = 30 V; T_{VJ} = 25°C		40	60	ns
I_{RM}	V_R = 540 V; I_F = 20 A; $-di_F/dt$ = 100 A/µs L ≤ 0.05 µH; T_{VJ} = 100°C		7		A

Features

- International standard package
- Glass passivated chips
- Very short recovery time
- Extremely low losses at high switching frequencies
- Low I_{RM}-values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

① I_{FAVM} rating includes reverse blocking losses at T_{VJM}, $V_R = 0.8\ V_{RRM}$, duty cycle d = 0.5
Data according to IEC 60747
IXYS reserves the right to change limits, test conditions and dimensions

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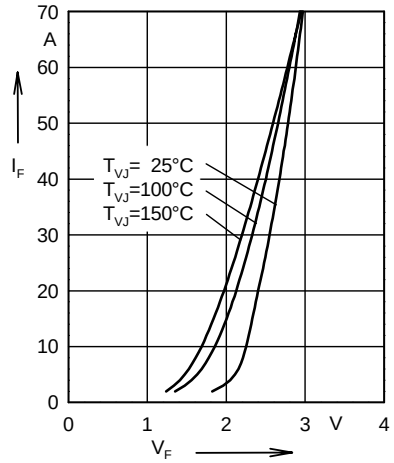


Fig. 1 Forward current versus voltage drop.

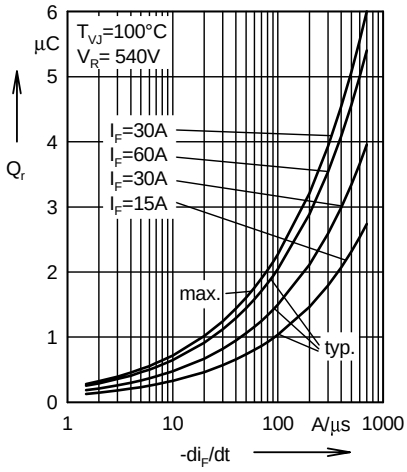


Fig. 2 Recovery charge versus $-di_F/dt$.

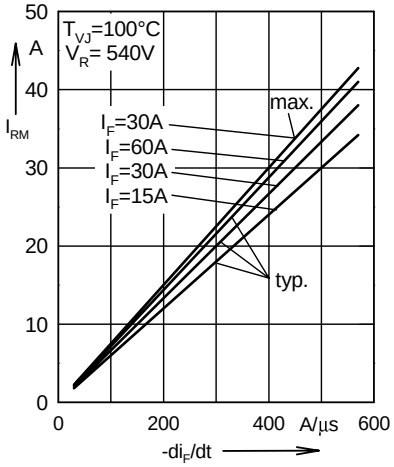


Fig. 3 Peak reverse current versus $-di_F/dt$.

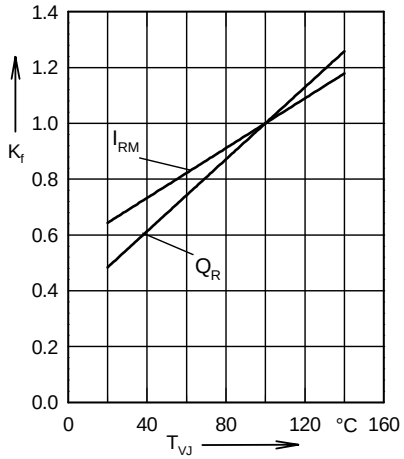


Fig. 4 Dynamic parameters versus junction temperature.

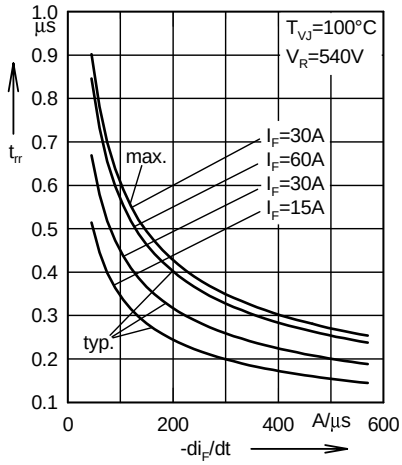


Fig. 5 Recovery time versus $-di_F/dt$.

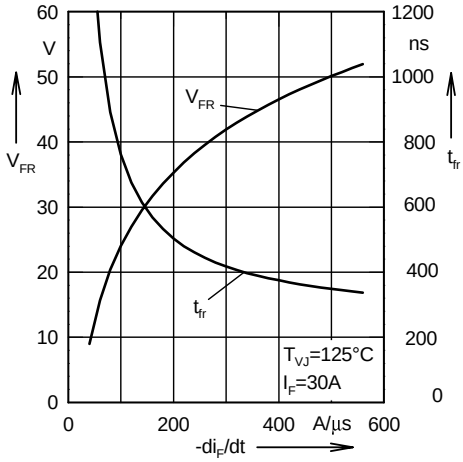


Fig. 6 Peak forward voltage versus di_F/dt.

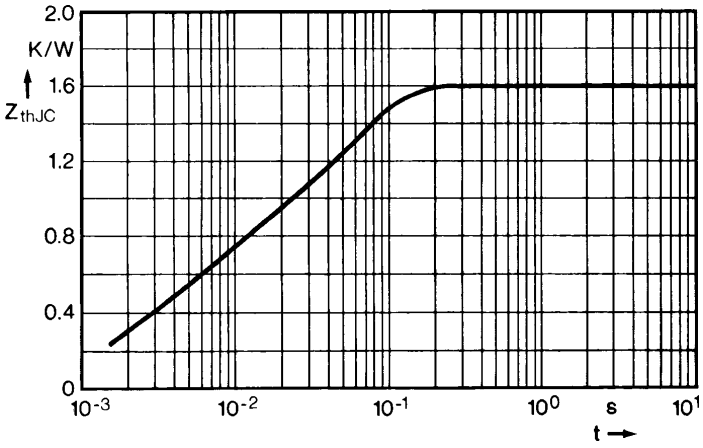
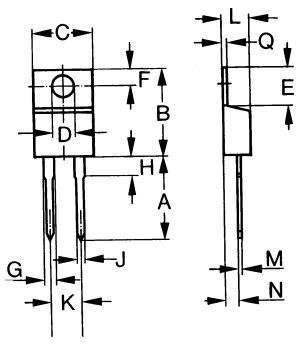


Fig. 7 Transient thermal impedance junction to case.

Dimensions



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	14.73	0.500	0.580
B	14.23	16.51	0.560	0.650
C	9.66	10.66	0.380	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.420
F	2.54	3.42	0.100	0.135
G	1.15	1.77	0.045	0.070
H	-	6.35	-	0.250
J	0.64	0.89	0.025	0.035
K	4.83	5.33	0.190	0.210
L	3.56	4.82	0.140	0.190
M	0.38	0.56	0.015	0.022
N	2.04	2.49	0.080	0.115
Q	0.64	1.39	0.025	0.055

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